

IN THE CLAIMS:

Kindly cancel claims 1-11 and 25, without prejudice, as being directed to a non-elected group. Kindly amend claims 20 and 22 as follows.

Replace claim 20 with the following amended claim:

sub 207
A3

20. (Amended) The method as claimed in claim 19, wherein the anti-reflection layer has a structure selected from the group consisting of: (i) a single-level structure comprised of one or more materials selected from the group consisting of Ti, Ta, Mo, TiN, TiW, TaN, and MoN; (ii) a multi-level structure comprised of one or more materials selected from the group consisting of W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N; and (iii) combination layers thereof.

The changes in the previous paragraph are indicated by brackets for deletions and underlining for insertions.

20. (Amended) The method as claimed in claim 19, wherein the anti-reflection layer has a structure selected from the group consisting of: (i) a single-level structure comprised of one or more materials selected from the group consisting of Ti, Ta, Mo, TiN, TiW, TaN, and MoN; (ii) a multi-level structure comprised of one or more materials selected from the group consisting of W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N; and (iii) [mixtures] combination layers thereof.

Replace claim 22 with the following amended claim:

Sub B4
AH

22. (Amended) The method as claimed in claim 21, wherein the metal barrier layer has a structure selected from the group consisting of: (i) a single-level structure comprised of one or more materials selected from the group consisting of Ti, Ta, Mo, TiN, TiW, TaN, and MoN; (ii) a multi-level structure comprised of one or more materials selected from the group consisting of W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N; and (iii) combination layers thereof.

The changes in the previous paragraph are indicated by brackets for deletions and underlining for insertions.

22. (Amended) The method as claimed in claim 21, wherein the metal barrier layer has a structure selected from the group consisting of: (i) a single-level structure comprised of one or more materials selected from the group consisting of Ti, Ta, Mo, TiN, TiW, TaN, and MoN; (ii) a multi-level structure comprised of one or more materials selected from the group consisting of W-N, W-Si-N, Ta-Si-N, W-B-N, and Ti-Si-N; and (iii) [mixtures] combination layers thereof.